EAST Search History

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6,927410".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 10:55
L2	1	10/718070	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 11:13
L3	107551	electrical near resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 11:21
L4	12023	phase near change near (material or layers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 11:21
L5	300	3 same 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 11:22
L6	31	3 same 4 same increase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/01 11:22
S1	44729	wet near (etch or etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 16:55
S2	155209	molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 09:55
S3	4872373	aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al. sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 09:55
S 5	2536	spray and immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 09:56

S6	41	S5 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 09:56
S7	108810	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 09:56
S8	3	S6 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:00
S9	4433577	(wet adj etch) and aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al.sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:00
S10	4432714	(wet adj etch) near aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al.sub.2" or "Al. sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:12
S11	10	(wet adj etch) near molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:01
S12	94761	S10 and molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:13
S13	484	S12 and immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:13
S14	162	S13 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:21
S19	37917	etch.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:17
S20	1	S14 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:17

S21	274	etching near molybdenum	US-PGPUB;	OR	ON	2005/08/24
OL 1	E / T		USPAT; EPO; JPO; DERWENT; IBM_TDB	ST		10:22
S22	51	etching near molybdenum.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:41
S23	2	S22 and LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:26
S24	2	"6797621".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:30
S26	14	(etching near aluminum.ab.) and hydrogen adj peroxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:31
S27	0	(molybdenum and aluminum) near selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:43
S28	7737	molybdenum and aluminum and selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:42
S29	0	(moly and al) near selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:42
S30	0	(moly and al) near selectively	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:43
S31	0	(molybdenum and aluminum) near selectively	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:43
S32	O	(molybdenum and aluminum) near selective	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:28

S33	0	(molybdenum and aluminum) near stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:44
S34	616	(molybdenum and aluminum) near layers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 10:44
S35	43	S34 and (wet near etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:50
S36	0	etch near aluminum near molybdem	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:51
S37	33	wet adj etch near aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:51
S39	3	S37 and molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:57
S40	1	06104241A	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:53
S41	10	wet adj etch near molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:58
S42	9	S41 and aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 11:58
S43	5	"6,686,280"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 15:05
S44	2	"6,686,280".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/24 15:05

		WC74C00FII ===	ELIC DODLID.	OD	ON	0005/00/04
S45	2	"6746925".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:08
S46	1	10/733722	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:07
S47	2	09/358983	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:14
S48	14316	wet near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:15
S49	460261	spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:15
S50	740	emmers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:15
S51	363574	immers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:15
S52	364247	S50 or S51	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:16
S53	201198	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:16
S54	16430	S52 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:17
S55	296	S52 near S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:11

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S56	9143	S53 and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:17
S57	281	S49 near S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 09:18
S58	4904937	aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al. sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S59	740	emmers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S60	363574	immers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S61	364247	S59 or S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S62	201198	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S63	296	S61 near S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S64	163	S58 and S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S65	460261	spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:12
S66	281	S65 near S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:49

S67	116	S58 and S66	US-PGPUB;	OR	ON	2005/09/21
	-		USPAT; EPO; JPO; DERWENT; IBM_TDB			11:12
S68	1551750	selective or selectively or selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:13
S69	68	S64 and S68	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:13
S70	58	S67 and S68	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:13
S71	3	S69 and S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:38
S72	564903	etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:42
S73	3884	thin adj film adj heads	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:39
S74	1376	S72 and S73	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:46
S75	135	etch adj rate adj more	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:39
S76	147	etch adj rate adj fast\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:39
S77	197	etch adj rate adj slow\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:40

S78	242	etch adj rate adj less	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:40
S79	681	S75 S76 S77 S78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:40
S80	4	S74 and S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:40
S81	178	"48" and S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:43
S82	163	S81 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:43
S83	402	S72 and S73 and "48"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:47
S84	348	S83 and steps	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:47
S85	1	S63 near S66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:50
S86	129	spray near immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 11:58
S87	33	S86 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:06
S88	0	spray adj then adj immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:06

S89	0	sray same immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:06
S90	786	spray same immerse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:06
S91	338	S90 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:12
S92	1736311	S91 and thin adj film ard heads	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:12
S93	3626038	j	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:12
S96	2	S91 and LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:16
S97	540	LCD and (wet adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:16
S100	27	S97 and S61 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:42
S102	192817	LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:43
S103	5	S102 and S90	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:46
S104	0	multi-layered adj liqiud adj crystal adj display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:48

S105	10	liqiud adj crystal adj display	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:48
S106	192817	lcd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:48
S107	192826	S105 or S106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:48
S108	2410	S107 and (wet adj etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:49
S109	55	S108 and spray and immers\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:55
S110	13014	S62 and taper\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:55
S111	98762	"55" and taper\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 12:56
S112	22	S109 and taper\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 13:01
S113	201312	latteral etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 13:02
S116	26	wet adj etch\$3 adj chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 13:12
S117	22	taper\$3 adj (wet adj etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 13:38

S118	121	side-etch	US-PGPUB;	OR	ON	2005/09/21
			USPAT; EPO; JPO; DERWENT; IBM_TDB			13:38
S119	1612	side-etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 13:38
S120	74	S119 and LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:03
S121	4	S120 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:21
S122	33	S119 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:42
S123	2	S122 and paddle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:22
S124	0	wet adj etch adj conveyor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:43
S125	43	wet adj etch and conveyor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:43
S126	5	S125 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/21 14:52
S128	14408	wet near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:56
S130	461507	spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:58

S131	143055	immerse or immersion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:57
S132	20562	S130 and S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:58
S133	152	S128 and S132	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:58
S135	4916426	aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al. sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:59
S136	130	S133 and S135	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 07:59
S138	156567	molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:02
S140	21	S136 and S138	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:03
S141	192035			OR	ON	2005/09/29 08:05
S142	268933	(acetic adj acid) or (CH3COOH or CH3COOHChsub3COOH or "CH. sub.3.COOH" or CHxCOOH or "CH. sub.x.COOH" or CHsubxCOOH) or HAc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:06
S143	102330	(Nitric adj acid) or (HNO3 or HNOx or HNOn or HNOsubx or HNOsubn or "HNO.subx" or "HNO. subn" or "HNO.sub.x" or "HNO. sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:06
S144	957	S141 near S142 near S143	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:07

S145	556	S144 and aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:07
S146	93	S145 and spray	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:09
S147	628	two near step near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:09
S148	20	S146 and S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:11
S149	1751	side near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:11
S150	6652	side near slope	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:11
S151	10	S149 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:14
S152	109927	S135 and S138	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:15
S153	226610	TFT or LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:15
S154	5924	S152 and S153	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:15
S155	258	S154 and (wet near etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:15

S156	6	S155 and spray	US-PGPUB;	OR	ON	2005/09/29
			USPAT; EPO; JPO; DERWENT; IBM_TDB			09:31
S157	2	"20030220708"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:41
S158	1	molybdenum near (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:14
S159	116	(Silicon adj dioxide) near (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:14
S160	80	molybdenum same (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:14
S161	3	S159 and S160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:16
S162	4	(refractory adj metal) near (hard adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:23
S163	2	"5302547".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:27
S164	3	(molybdenum near layered) same aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:29
S165	4	(molybdenum near top near bottom) same aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:35
S166	0	"10704562"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:35

S167	1	10/704562	US-PGPUB;	OR	ON	2005/09/29
			USPAT; EPO; JPO; DERWENT; IBM_TDB			11:36
S168	306313	stacked	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:36
S169	156567	molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:36
S170	4916426	aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al. sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:36
S171	1	S168 near S169 near S170	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:59
S172	156567	molybdenum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:59
S173	4916426	aluminum or (Al OR Al2 or Alsub2 or "Al.subx" or "Al.subn" or "Al. sub.2" or "Al.sub.x" or "Al.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:59
S174	2610	S172 near S173 near S172	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:02
S176	193977	lcd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:00
S177	326	S174 and S176	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:00
S178	294	S177 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:00

S179	91	S178 and etch	US-PGPUB; USPAT; EPO;	OR	ON	2005/09/29 13:00
			JPO; DERWENT; IBM_TDB			13.00
S180	4922	(S172 near S173) same (S173 near S172)	US PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:02
S181	4922	(S172 near S173) with (S173 near S172)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:02
S182	4922	(S172 near S173) and (S173 near S172)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:03
S183	425	S180 and S176	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:03
S184	0	"L1 near L2" and "L2 near L1"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:04
S185	1331	(S172 adj4 S173) and (S173 adj4 S172)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:05
S186	802	(S172 adj4 S173) same (S173 adj4 S172)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:05
S187	138	S186 and lcd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:05
S188	1705869	S187 and etch or remove	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 13:06
S189	65	S187 and (etch or remove)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:56

S190	2	"6531377".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:57
S191	1	10/732931	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:57
S192	2	"6927410".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 14:37
S193	0	"10718070"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 14:37
S194	1	10/718070	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 14:37
S195	2	"6943365".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 16:59
S196	2	"6927410".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 17:30
S197	2	"5536947".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:38
S198	79	(("same" or similar) near resistivity) and (different near resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:40
S199	23	S198 and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:41
S200	180082	S199 and memory or (memory near (bit or cell))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:41

S201	180082	S199 and memory or (memory near (bit or cell))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:41
S202	19	S199 and S201	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:44
S203	10	S202 and ((multi-bit) or (mutiple near bit))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:52
S204	681	multi-bit adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:52
S205	87	multi-bit adj memory.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:52
S206	701	phase near change near memory near device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:23
S207	0	phase near change near "same" near dimensions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:22
S208	0	phase near change near "same" near dimentions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:22
S209	4	S206 and ("same" near dimensions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:24
S210	1906	phase near change near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:24
S211	8	S210 and ("same" near dimensions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:24

S213	6	"5536947".pn. or "6927410".pn. or "6943365".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 18:17
S214	2	S213 and (dope or doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 18:18
S215	0	S213 and (crystalization near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 18:18
S216	0	S213 and (crystal near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 18:18
S217	26	GST and implant and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:11
S218	26	("e.sub.2Sb.sub.2Te.sub.5" or GST) and implant and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:11
S219	41	("Ge.sub.2Sb.sub.2Te.sub.5" or GST) and implant and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:12
S220	0	(("Ge.sub.2Sb.sub.2Te.sub.5" or GST) near implant) and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:11
S221	1	(("Ge.sub.2Sb.sub.2Te.sub.5" or GST) same implant) and (phase near change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:20
S222	4	(("Ge.sub.2Sb.sub.2Te.sub.5" or GST) same implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:25
S223	2	"7005665".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:24

S224	3	(("Ge2Sb2Te5" or GST) same implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:31
S225	7	"1439579".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:29
S226	183	(("Ge2Sb2Te5" or GST) same nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:31
S227	31	S226 and (phase adj change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 09:31

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